P-Ch 60V Fast Switching MOSFETs

★ 100% EAS Guaranteed
★ Green Device Available
★ Super Low Gate Charge
★ Excellent CdV/dt effect decline
★ Advanced high cell density Trench technology

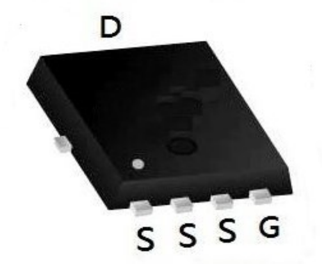
Product Summary

BVDSS	RDSON	ID
-60V	24mΩ	-30A

Description

The XR30P06F is the high cell density trenched P-ch MOSFETs, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.
The XR30P06F meet the RoHS and Green Product requirement, 100% EAS guaranteed with full function reliability approved.

PDFN5060-8L Pin Configuration



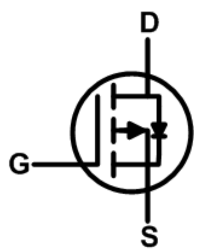


Table 1. Absolute Maximum Ratings (T_A=25℃ unless otherwise noted)

Symbol	Parameter	Limit	Unit
V_{DS}	Drain-Source Voltage (V_{GS}=0V)	-60	V
V_{GS}	Gate-Source Voltage (V_{DS}=0V)	±20	V
I_D	Drain Current-Continuous(T_C=25℃)	-30	A
	Drain Current-Continuous(T_C=100℃)	-25.5	A
$I_{DM\ (pluse)}$	Drain Current-Continuous@ Current-Pulsed (Note 1)	-144	A
P_D	Maximum Power Dissipation(T_C=25℃)	79	W
	Maximum Power Dissipation(T_C=100℃)	39.5	W
E_{AS}	Avalanche energy (Note 2)	196	mJ
T_J, T_{STG}	Operating Junction and Storage Temperature Range	-55 To 175	℃

Table 2. Thermal Characteristic

Symbol	Parameter	Typ	Max	Unit
$R_{\theta JC}$	Thermal Resistance, Junction-to-Case		1.9	℃/W

Table 3. Electrical Characteristics (T_J=25℃ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
On/Off States						
BV_{DSS}	Drain-Source Breakdown Voltage	V_{GS}=0V I_D=-250μA	-60			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=-60V, V_{GS}=0V			-1	μA
I_{GSS}	Gate-Body Leakage Current	V_{GS}=±20V, V_{DS}=0V			±100	nA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS}, I_D=-250μA	-1	-1.8	-2.5	V
g_{FS}	Forward Transconductance	V_{DS}=-5V, I_D=-15A		35		S
$R_{DS(ON)}$	Drain-Source On-State Resistance	V_{GS}=-10V, I_D=-15A		24	30	mΩ
		V_{GS}=-4.5V, I_D=-10A		30	40	mΩ
Dynamic Characteristics						
C_{iss}	Input Capacitance	V_{DS}=-25V, V_{GS}=0V, f=1.0MHz		4026		pF
C_{oss}	Output Capacitance			134		pF
C_{rss}	Reverse Transfer Capacitance			98		pF
Switching Parameters						
$t_{d(on)}$	Turn-on Delay Time	V_{GS}=-10V, V_{DS}=-30V, R_L=1.5Ω, R_{GEN}=3Ω		12.2		nS
t_r	Turn-on Rise Time			10		nS
$t_{d(off)}$	Turn-Off Delay Time			64		nS
t_f	Turn-Off Fall Time			14		nS
Q_g	Total Gate Charge	V_{GS}=-10V, V_{DS}=-30V, I_D=-20A		68		nC
Q_{gs}	Gate-Source Charge			10.5		nC
Q_{gd}	Gate-Drain Charge			13		nC
Source-Drain Diode Characteristics						
I_{SD}	Source-Drain Current (Body Diode)				30	A
V_{SD}	Forward on Voltage (Note 3)	V_{GS}=0V, I_S=-15A			-1.2	V
t_{rr}	Reverse Recovery Time	I_F=-20A, di/dt=100A/μs		26		ns
Q_{rr}	Reverse Recovery Charge	I_F=-20A, di/dt=100A/μs		29		nC

Notes 1.Repetitive Rating: Pulse width limited by maximum junction temperature.
Notes 2.E_{AS} condition: T_J=25℃,V_{DD}=40V,V_G=-10V, Rg=25Ω, L=0.5mH.
Notes 3.Repetitive Rating: Pulse width limited by maximum junction temperature.

Typical Electrical And Thermal Characteristics (Curves)

Figure 1. Output Characteristics

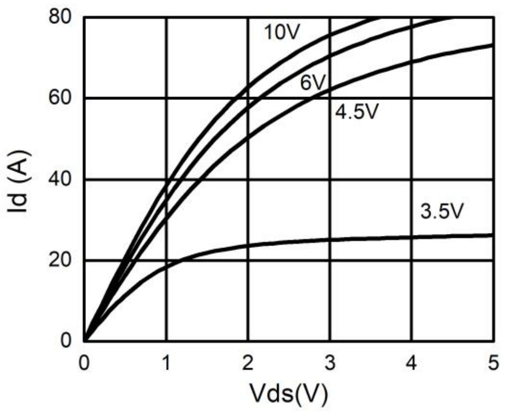


Figure 2. Transfer Characteristics

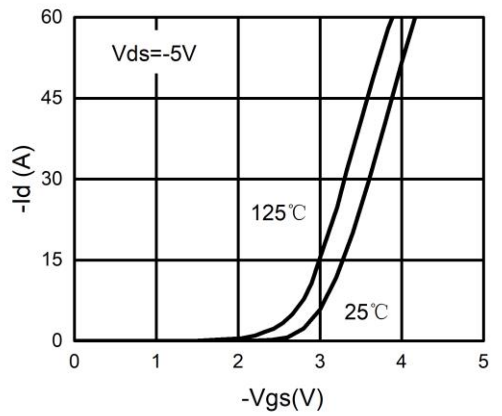


Figure 3. Power Dissipation

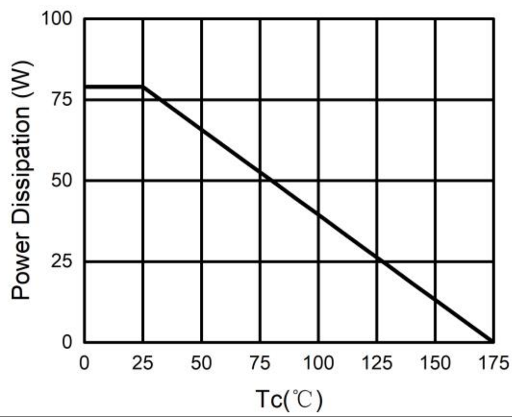


Figure 4. Drain Current

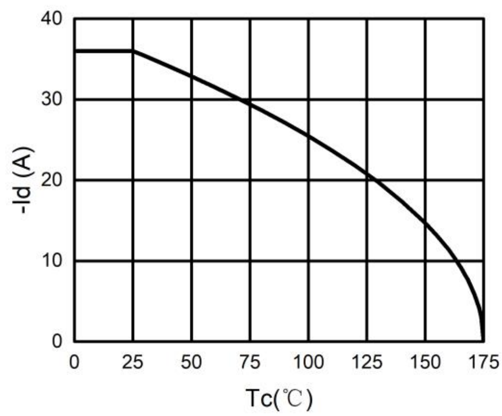


Figure 5. BV_{DSS} vs Junction Temperature

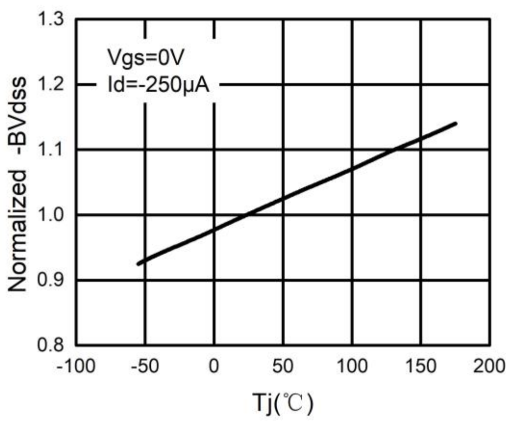


Figure 6. $R_{DS(ON)}$ vs Junction Temperature

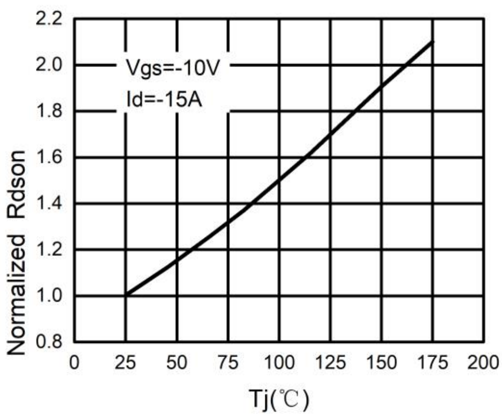


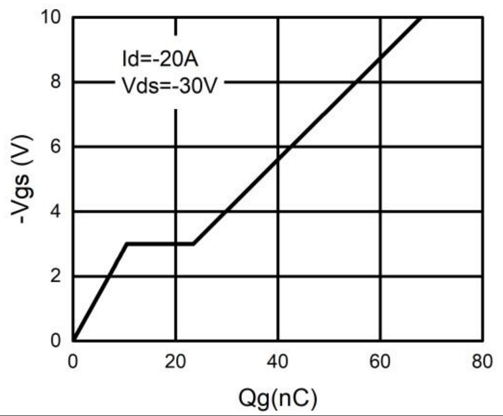
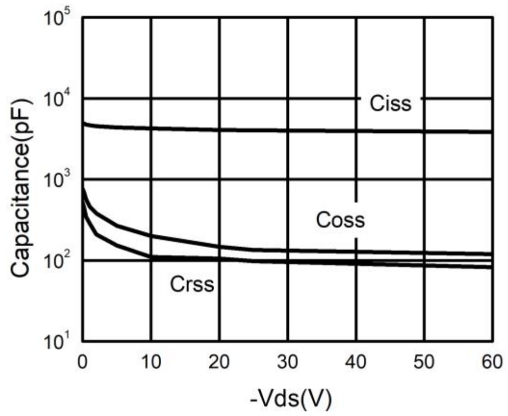
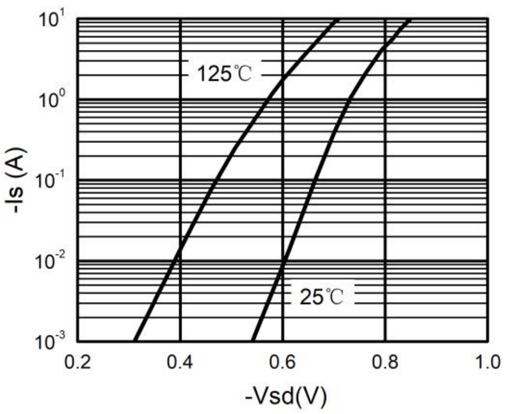
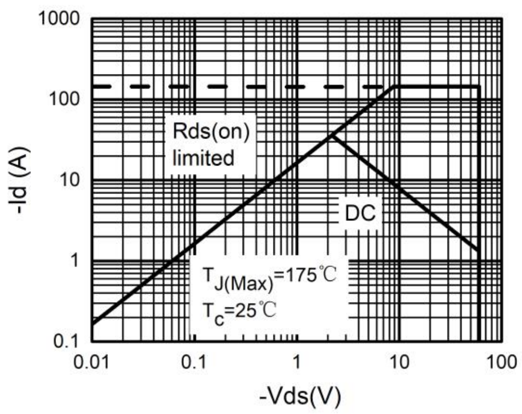
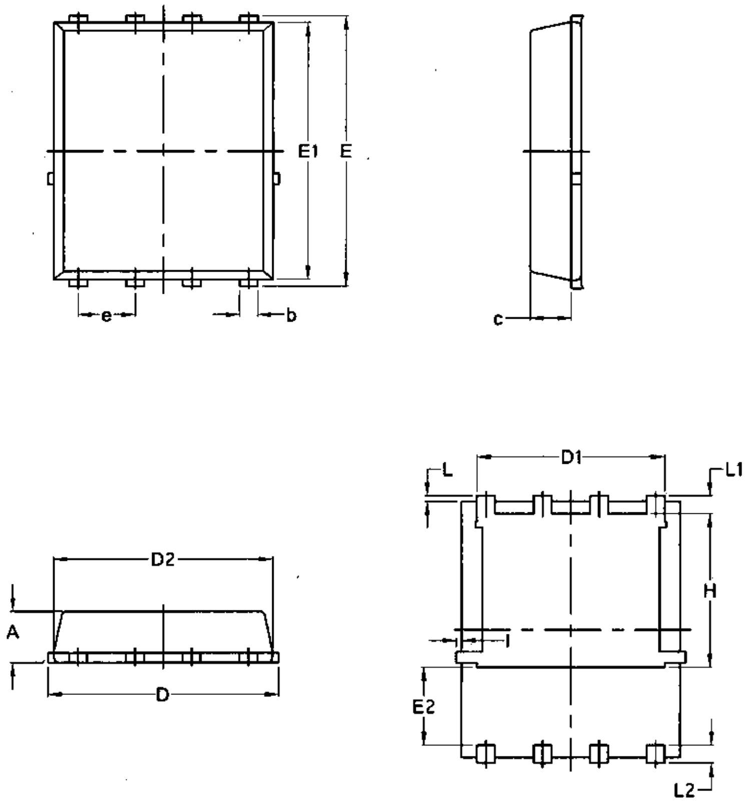
Figure 7. Gate Charge Waveforms	Figure 8. Capacitance
	

Figure 9. Body-Diode Characteristics	Figure 10. Maximum Safe Operating Area
	

Package Mechanical Data-PDFN5060-8L-JQ Single



Symbol	Common			
	mm		Inch	
	Mim	Max	Min	Max
A	1.03	1.17	0.0406	0.0461
b	0.34	0.48	0.0134	0.0189
c	0.824	0.0970	0.0324	0.082
D	4.80	5.40	0.1890	0.2126
D1	4.11	4.31	0.1618	0.1697
D2	4.80	5.00	0.1890	0.1969
E	5.95	6.15	0.2343	0.2421
E1	5.65	5.85	0.2224	0.2303
E2	1.60	/	0.0630	/
e	1.27 BSC		0.05 BSC	
L	0.05	0.25	0.0020	0.0098
L1	0.38	0.50	0.0150	0.0197
L2	0.38	0.50	0.0150	0.0197
H	3.30	3.50	0.1299	0.1378
I	/	0.18	/	0.0070